1. Scope :

This specification applies to PN silicon photodiode chips,
Device No. PD-0054

2. Structure :

2-1. Planar type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy.

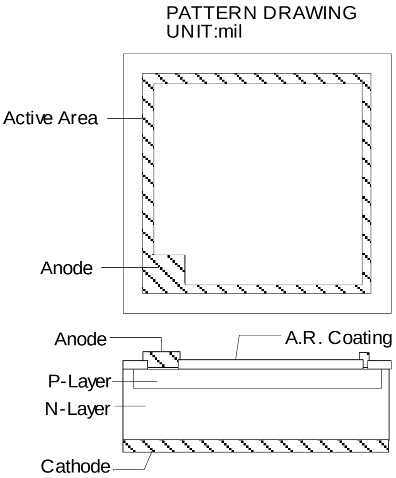
3. Size :

3-1. Chip size : 56 mils x 52 mils (1.422 mm x 1.320 mm).
3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).
3-3. Active area : 45 mils x 41 mils (1.143 mm x 1.041 mm).
3-4. Bonding pad (Anode) : 6.5 mils x 6.5 mils (0.165 mm x 0.165 mm).
3-5. Pattern drawing : Refer to the attached drawing.

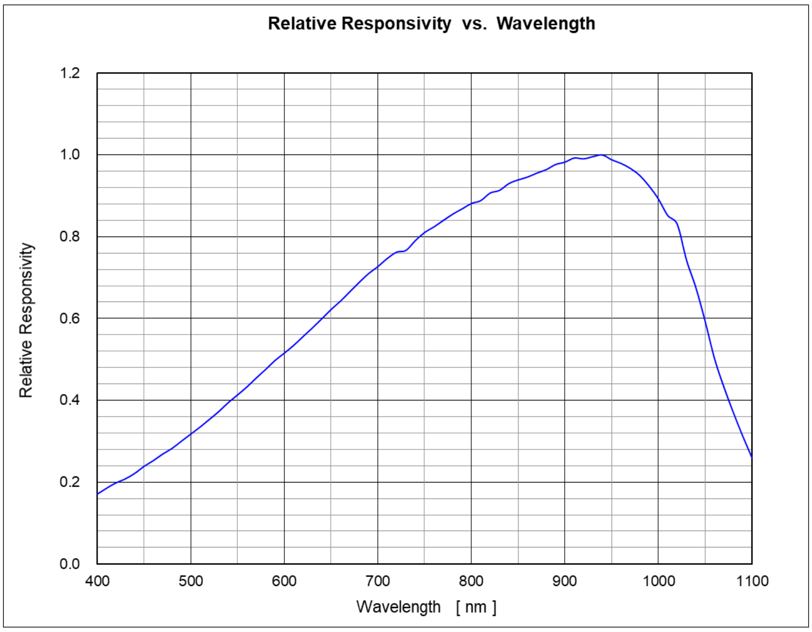
4. Electro-optical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark current	I_D	V_R=10V Ee=0mW/cm^2			5	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA Ee =0mW/cm^2	33			V
Short circuit Current	Isc	T=2856K Ee=5mW/cm^2		11		µA
Reverse light current	I_L	V_R =5V T=2856K Ee=5mW/cm^2		11		µA
Total Capacitance	C_t	V_R =5V Ee=0mW/cm^2 f=1MHz		16		pF

※Based on 100% probing



5. Relative spectral responsivity



※Bare chip measured with integrating sphere, for reference only.